

In re Patent Application of:
HILL
Serial No. 10/761,338
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IN THE DESCRIPTION

Please replace the paragraph extending from Page 11, lines 15 to Page 12, line 6 with:

Applicants U.S. provisional application 60/441,413 ~~<attorney docket 50422-1>~~ entitled "Preparation of type IV Semiconductor Nanocrystals Doped with Rare-earth Ions and Product Thereof" filed January 22, 2003 teaches methods of preparing group IV semiconductor nanocrystals doped with rare-earth ions. In one embodiment provided in that application, the invention provides a doped type IV semiconductor nanocrystal layer. In another aspect, the invention provides a doped type IV semiconductor nanocrystal powder comprising crystals of a group IV element that bear on their surface atoms of one or more rare earth elements. The powder can also be used to form a layer, for example by including the powder in a layer of a dielectric medium for example spun glass, or a polymer. That application is incorporated herein in its entirety by reference. Two regular U.S. applications 10/761,275 and 10/761,409 ~~<attorney dockets 50422-7; 50422-8~~ > based on the above provisional have been filed the same day as this application and are hereby incorporated by reference in their entirety. In the entire description that follows, whenever a rare-earth doped group IV semiconductor nanocrystal material (REDGIVN material) is referred to, any material taught in the incorporated documents is contemplated.